

## Silicon PNP Power Transistors

2SB975

## DESCRIPTION

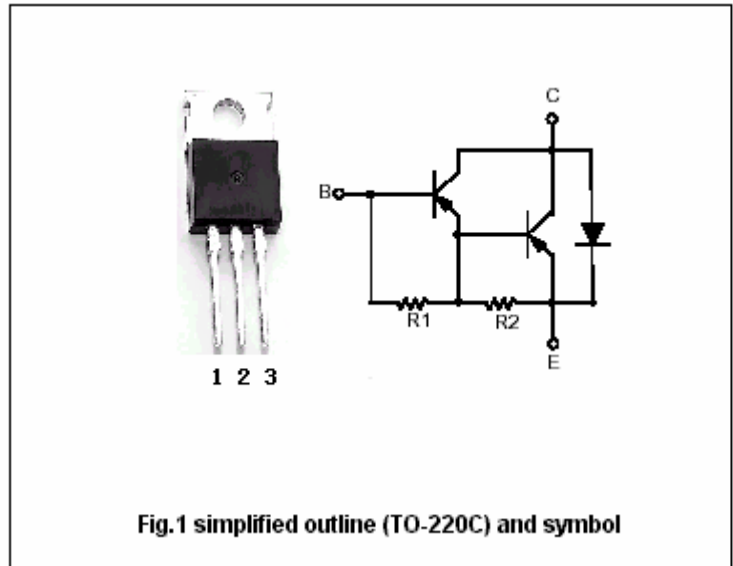
- With TO-220 package
- DARLINGTON
- High DC current gain
- Low collector saturation voltage

## APPLICATIONS

- Low frequency power amplification
- Low speed power switching applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-100	V
$V_{CEO}$	Collector-emitter voltage	Open base	-100	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-8	A
$P_C$	Collector power dissipation	$T_C=25^\circ\text{C}$	40	W
		$T_a=25^\circ\text{C}$	1.5	
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEQ(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =-30mA ; I <sub>B</sub> =0	-100			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-1mA ; I <sub>E</sub> =0	-100			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-5mA ; I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-3A; I <sub>B</sub> =-3mA			-1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-3A; I <sub>B</sub> =-3mA			-2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-100V; I <sub>E</sub> =0			-1	μA
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =-50V; I <sub>B</sub> =0			-100	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-5.0	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-3A ; V <sub>CE</sub> =-2V	2000		15000	

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PACKAGE OUTLINE

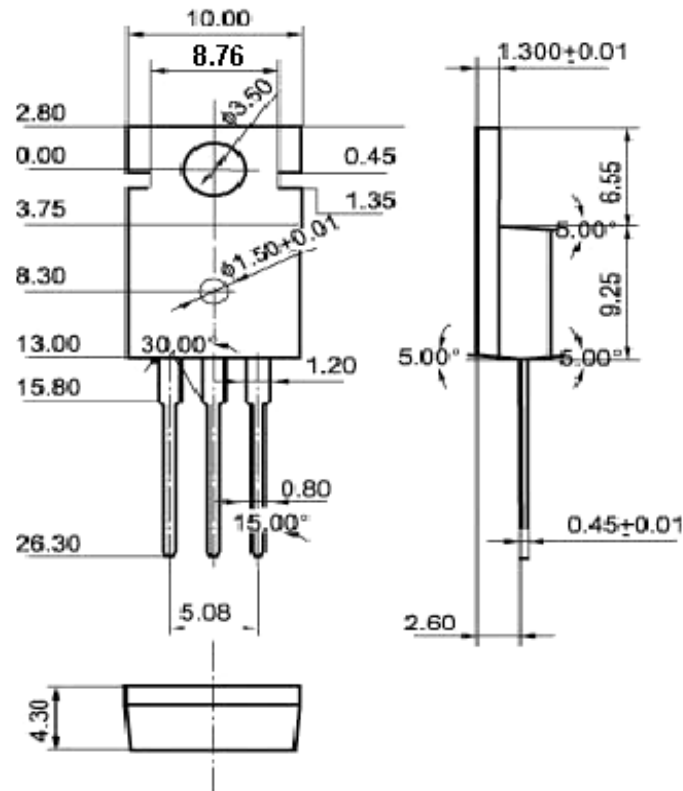


Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)